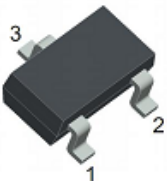
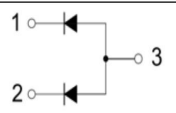
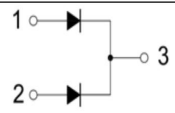
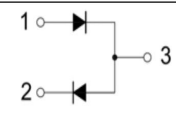
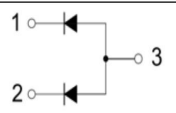
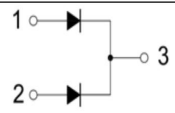
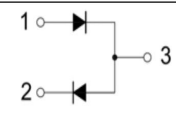
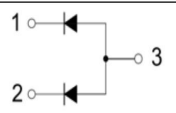
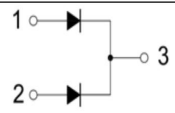
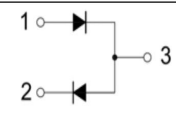


Switching Diodes	SOT-23 Plastic-Encapsulate Diodes										
<p><u>SOT-23</u></p> 	<p>Features</p> <ul style="list-style-type: none"> • High Conductance • Fast Switching Speed • For General Purpose Switching Applications 										
<table border="1" style="width: 100%;"> <tr> <th style="width: 33%;">BAW56</th> <th style="width: 33%;">BAV70</th> <th style="width: 33%;">BAV99</th> </tr> <tr> <td style="text-align: center;">  </td> <td style="text-align: center;">  </td> <td style="text-align: center;">  </td> </tr> <tr> <td style="text-align: center;">MARKING:A1</td> <td style="text-align: center;">MARKING:A4</td> <td style="text-align: center;">MARKING:A7</td> </tr> </table>	BAW56	BAV70	BAV99				MARKING:A1	MARKING:A4	MARKING:A7		
BAW56	BAV70	BAV99									
											
MARKING:A1	MARKING:A4	MARKING:A7									

Solid dot = Green molding compound device, if none, the normal device.

Maximum ratings (@Ta=25°C)

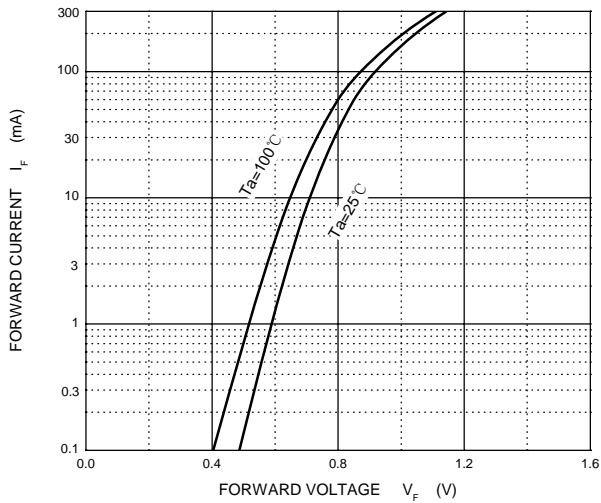
Parameter	Symbol	Limit	Unit
Reverse Voltage	VR	70	V
Forward Current	IF	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	IFSM	2.0	A
Power Dissipation	PD	225	mW
Thermal Resistance from Junction to Ambient	RθJA	556	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55~+150	°C

Electrical Characteristics (@Ta=25°C)

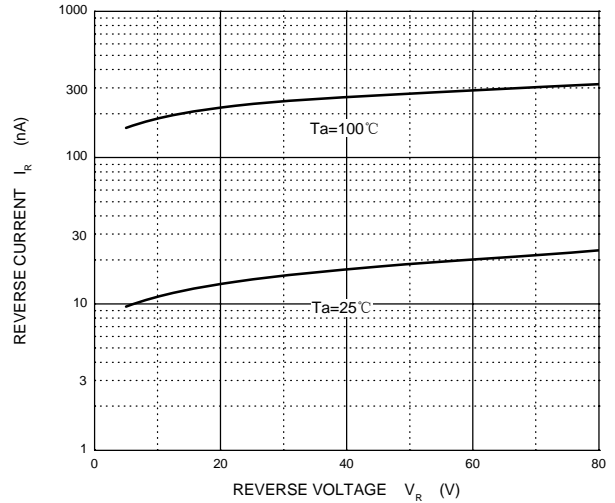
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse breakdown voltage	V(BR)	IR=100µA	70			V
Forward voltage	VF1	IF=1mA		0.57	0.715	V
	VF2	IF=10mA		0.714	0.855	V
	VF3	IF=50mA		0.83	1	V
	VF4	IF=150mA		0.97	1.25	V
Reverse current	IR	VR=70V			2.5	uA
capacitance Between terminals	Ctot	VR=0V,f=1MHz			1.5	PF
Reverse recovery time	t _{rr}	IF=IR=10mA, I _{rr} =0.1×IR,RL= 100Ω			6	nS

Typical Characteristics

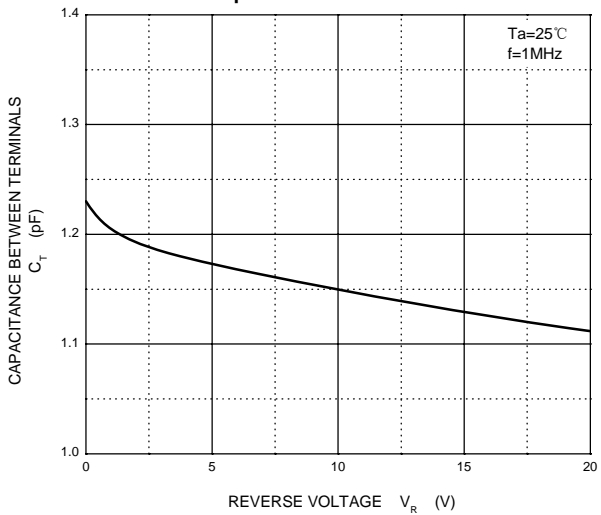
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

